

Petr Klenovsky

List of Publications by Year in descending order

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29
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397
citing authors

#	ARTICLE	IF	CITATIONS
1	Modeling electronic and optical properties of III-V quantum dots—selected recent developments. Light: Science and Applications, 2022, 11, 17.	7.7	20
2	Dimension-Dependent Phenomenological Model of Excitonic Electric Dipole in InGaAs Quantum Dots. Nanomaterials, 2022, 12, 719.	1.9	2
3	Interplay between multipole expansion of exchange interaction and Coulomb correlation of exciton in colloidal II-VI quantum dots. Electronic Structure, 2022, 4, 015006.	1.0	6
4	Excitonic fine structure of epitaxial Cd(Se,Te) on ZnTe type-II quantum dots. Physical Review B, 2022, 105, .	1.1	2
5	Structural and compositional analysis of (InGa)(AsSb)/GaAs/GaP Stranski-Krastanov quantum dots. Light: Science and Applications, 2021, 10, 125.	7.7	14
6	On the importance of antimony for temporal evolution of emission from self-assembled (InGa)(AsSb)/GaAs quantum dots on GaP(001). New Journal of Physics, 2021, 23, 103029.	1.2	10
7	Electric field induced tuning of electronic correlation in weakly confining quantum dots. Physical Review B, 2021, 104, .	1.1	15
8	Theory of magneto-optical properties of neutral and charged excitons in GaAs/AlGaAs quantum dots. Physical Review B, 2020, 102, .	1.1	22
9	Optical response of (InGa)(AsSb)/GaAs quantum dots embedded in a GaP matrix. Physical Review B, 2019, 100, .	1.1	19
10	Electronic states of (InGa)(AsSb)/GaAs/GaP quantum dots. Physical Review B, 2019, 100, .	1.1	23
11	Assessing Carrier Recombination Processes in Type-II SiGe/Si(001) Quantum Dots. Annalen Der Physik, 2019, 531, 1800259.	0.9	7
12	Optical orientation and alignment of excitons in direct and indirect band gap (In,Al)As/AlAs quantum dots with type-I band alignment. Physical Review B, 2019, 99, .	1.1	19
13	Single-particle-picture breakdown in laterally weakly confining GaAs quantum dots. Physical Review B, 2019, 100, .	1.1	26
14	Resolving the temporal evolution of line broadening in single quantum emitters. Optics Express, 2019, 27, 35290.	1.7	23
15	Effect of second-order piezoelectricity on the excitonic structure of stress-tuned In(Ga)As/GaAs quantum dots. Physical Review B, 2018, 97, .	1.1	20
16	Excitonic structure and pumping power dependent emission blue-shift of type-II quantum dots. Scientific Reports, 2017, 7, 45568.	1.6	36
17	Inversion of the exciton built-in dipole moment in In(Ga)As quantum dots via nonlinear piezoelectric effect. Physical Review B, 2017, 96, .	1.1	23
18	Ellipsometry of surface layers on a 1-kg sphere from natural silicon. Applied Surface Science, 2017, 421, 542-546.	3.1	3

#	ARTICLE	IF	CITATIONS
19	Type-II InAs/GaAsSb/GaAs Quantum Dots as Artificial Quantum Dot Molecules. Acta Physica Polonica A, 2016, 129, A-62-A-65.	0.2	11
20	Type-I and Type-II Confinement in Quantum Dots: Excitonic Fine Structure. Acta Physica Polonica A, 2016, 129, A-66-A-69.	0.2	3
21	Excitonic fine structure splitting in type-II quantum dots. Physical Review B, 2015, 92, .	1.1	22
22	Polarization anisotropy of the emission from type-II quantum dots. Physical Review B, 2015, 92, .	1.1	20
23	Excitation intensity dependence of photoluminescence spectra of SiGe quantum dots grown on prepatterned Si substrates: Evidence for biexcitonic transition. Physical Review B, 2012, 86, 085411. Strain-induced anticrossing of bright exciton levels in single self-assembled GaAs/AlGaAs quantum dots. Physical Review B, 2012, 86, 085411.	1.1	17
24	Strain-induced anticrossing of bright exciton levels in single self-assembled GaAs/AlGaAs quantum dots. Physical Review B, 2012, 86, 085411.	1.1	76
25	Quantum entanglement in lateral GaAs/AlGaAs quantum dot molecules. Journal of Physics: Conference Series, 2010, 245, 012027.	0.3	15
26	Modelling of electronic states in InAs/GaAs quantum dots with GaAsSb strain reducing overlayer. Journal of Physics: Conference Series, 2010, 245, 012086.	0.3	17
27	Electronic structure of InAs quantum dots with GaAsSb strain reducing layer: Localization of holes and its effect on the optical properties. Applied Physics Letters, 2010, 97, 203107.	1.5	37
28	Characterization of near-field optical microscope probes. Surface and Interface Analysis, 2008, 40, 482-485.	0.8	1